NSN 5962-01-420-9577

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View Online at https://aerobasegroup.com/nsn/5962-01-420-9577

Body Length:	
0.358 inches	
Body Width: 0.358 inches	
Body Height:	
0.100 inches	
Maximum Power Dissipation Rating:	
1.0 watts	
Operating Tempurature Range:	
-55.0/+125.0 degrees celsius	
Storage Tempurature Range:	
-65.0/+150.0 degrees celsius	
End Application:	
Pacer dawn	
Features Provided:	
Electrostatic sensitive and monolithic and programmed and 3-state output and bipolar	
Inclosure Material:	
Ceramic and glass	
Inclosure Configuration:	
Leadless flat pack	
Output Logic Form:	
Transistor-transistor logic	
Input Circuit Pattern:	
14 input	
Criticality Code Justification:	
Cbbl	
Case Outline Source And Designator:	
C-4 mil-m-38510	
Terminal Surface Treatment:	
Solder	
Product Name:	
Microcircuit, programmed (prom 93z665a)	
Voltage Rating And Type Per Characteristic:	
-0.3 volts power source and 7.0 volts power source	
Time Rating Per Chacteristic:	
55.00 nanoseconds propagation delay time, high to low level output and 55.00 nanoseconds propagation delay tir	me, low to high level
output	-
Memory Device Type:	
Programmed	
Special Features:	
Altered item mode from device 92000022x, eage 14022, microsireuit, memory, digital, hipplar 64k (9k x 9) prom	

Altered item, made from device 82009023x, cage 14933, microcircuit, memory, digital, bipolar 64k (8k x 8) prom, monolithic silicon; program p/n 7816354p758

Test Data Document:

96906-mil-std883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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Terminal Type And Quantity:

20 leadless

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

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